



No.5296A

2SJ381

P-Channel MOS Silicon FET

Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Absolute Maximum Ratings at Ta = 25°C

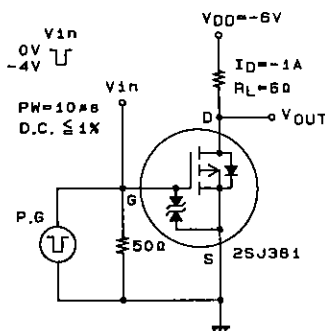
			unit
Drain-to-Source Voltage	V _{DSS}	-12	V
Gate-to-Source Voltage	V _{GSS}	±10	V
Drain Current (DC)	I _D	-2	A
Drain Current (Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	A
Allowable Power Dissipation	P _D	Tc = 25°C	3.5
		Mounted on ceramic board (250mm ² × 0.8mm)	1.5
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-12			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = -10V, V _{GS} = 0			-100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -6V, I _D = -1mA	-0.5		-1.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -6V, I _D = -1A	1.6	2.4		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D = -1A, V _{GS} = -4V		280	400	mΩ
ON-State Resistance	R _{DS(on)}	I _D = -500mA, V _{GS} = -2.5V		400	700	mΩ
Input Capacitance	C _{iss}	V _{DS} = -6V, f = 1MHz		170		pF
Output Capacitance	C _{oss}	V _{DS} = -6V, f = 1MHz		140		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -6V, f = 1MHz		40		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		20		ns
Rise Time	t _r	"		90		ns
Turn-OFF Delay Time	t _{d(off)}	"		100		ns
Fall Time	t _f	"		100		ns
Diode Forward Voltage	V _{SD}	I _S = -2A, V _{GS} = 0	-1.0	-1.2		V

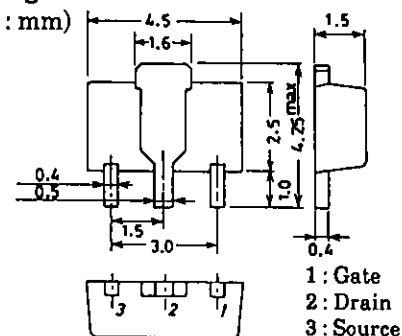
Marking : JI

Switching Time Test Circuit



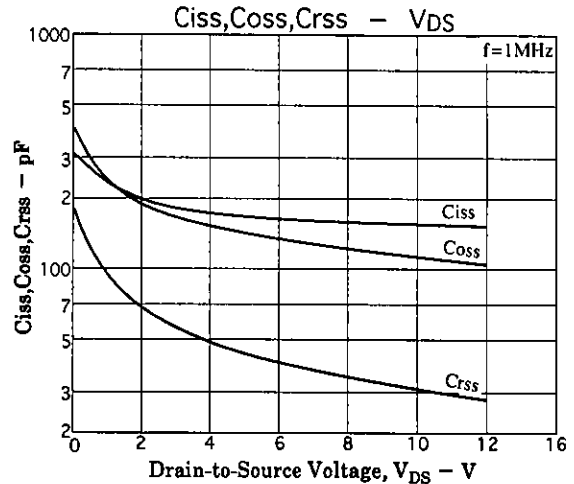
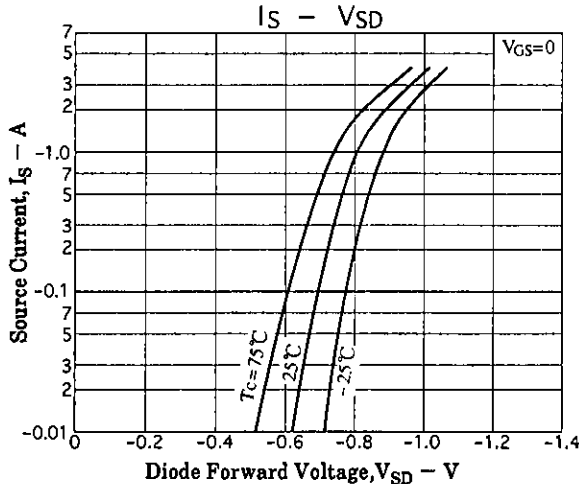
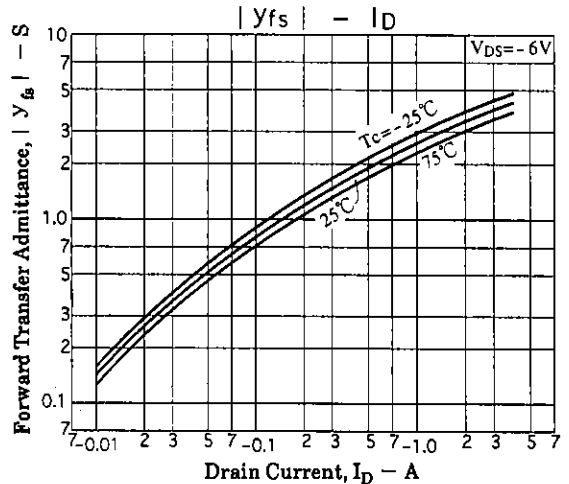
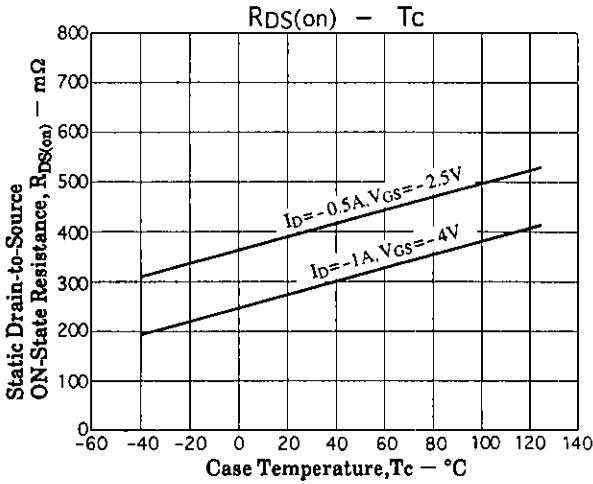
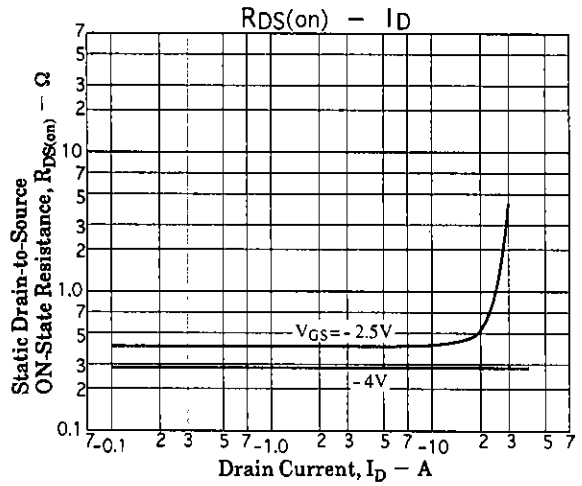
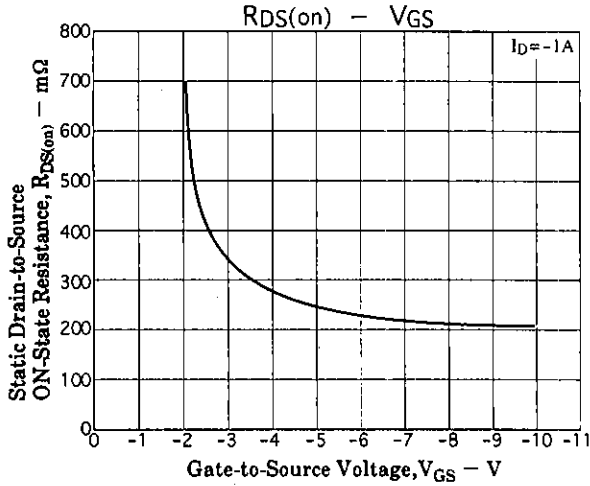
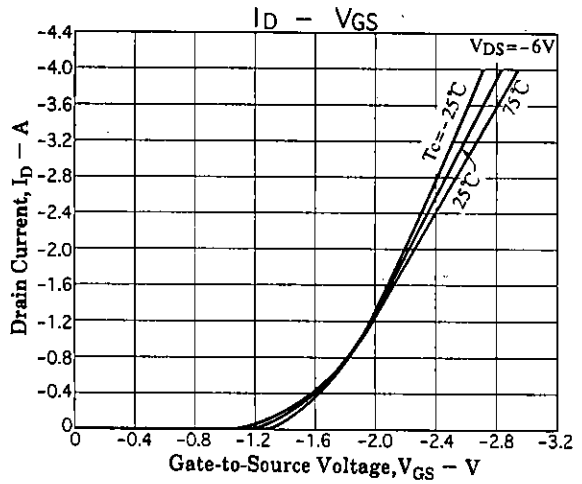
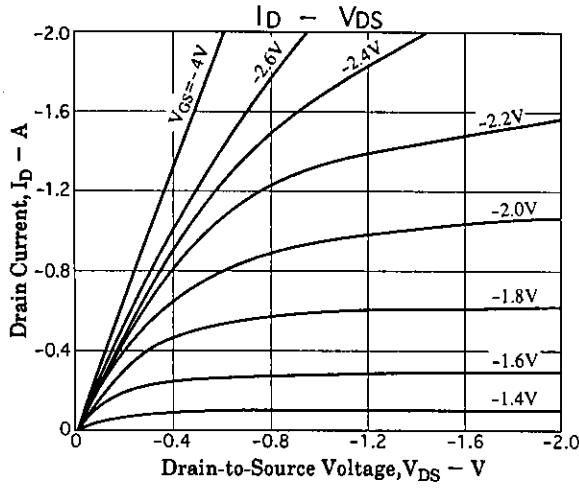
Package Dimensions 2062A

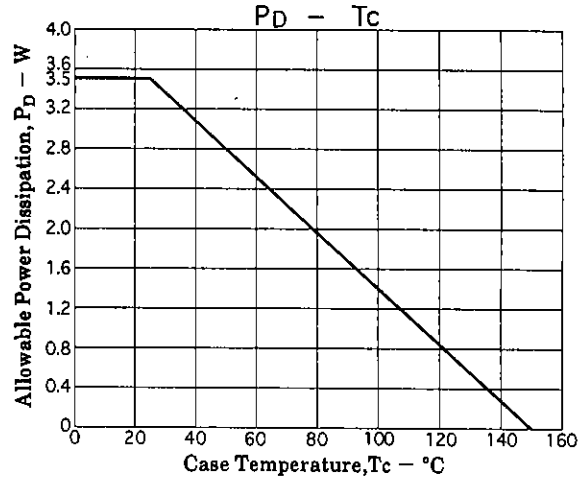
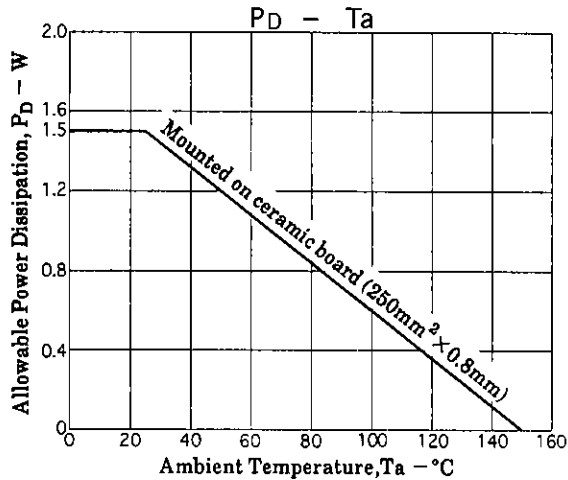
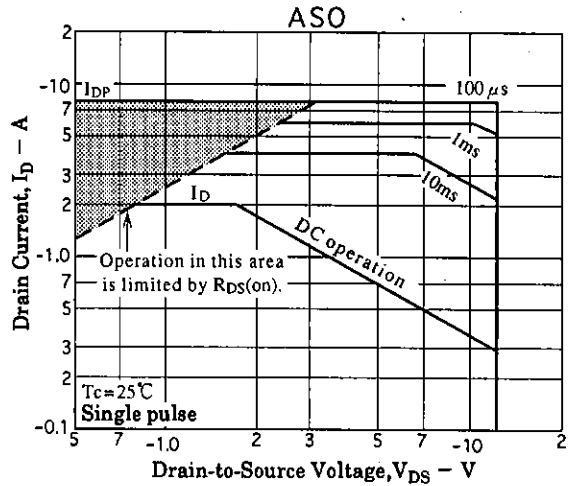
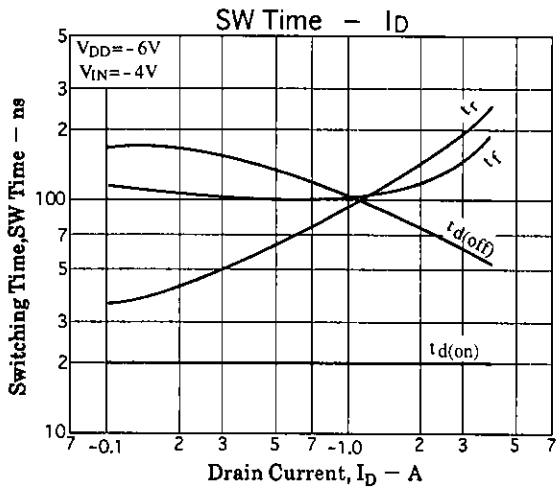
(unit : mm)



SANYO : PCP
(Bottom View)

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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